

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

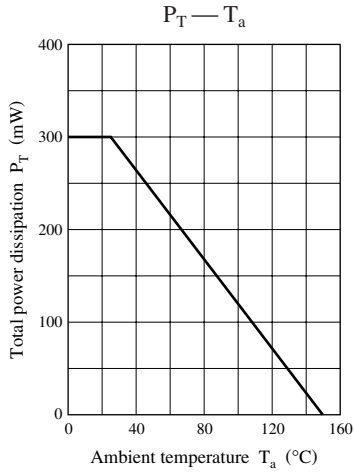
Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)		V_{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)		V_{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)		I_{CBO}	$V_{CB} = 50 \text{ V}, I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)		I_{CEO}	$V_{CE} = 50 \text{ V}, I_B = 0$			0.5	μA
Emitter-base cutoff current (Collector open)	UNR4210/4215/4216/4217	I_{EBO}	$V_{EB} = 6 \text{ V}, I_C = 0$			0.01	mA
	UNR4213					0.1	
	UNR4212/4214/421D/421E					0.2	
	UNR4211					0.5	
	UNR421F/421K					1.0	
	UNR4219					1.5	
	UNR4218/421L					2.0	
Forward current transfer ratio	UNR4218/421K/421L	h_{FE}	$V_{CE} = 10 \text{ V}, I_C = 5 \text{ mA}$	20			—
	UNR4219/421D/421F			30			
	UNR4211			35			
	UNR4212/421E			60			
	UNR4213/4214			80			
	UNR4210*/4215*/4216*/4217*			160		460	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$			0.25	V
Output voltage high-level		V_{OH}	$V_{CC} = 5 \text{ V}, V_B = 0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	4.9			V
Output voltage low-level		V_{OL}	$V_{CC} = 5 \text{ V}, V_B = 2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			0.2	V
	UNR4213/421K		$V_{CC} = 5 \text{ V}, V_B = 3.5 \text{ V}, R_L = 1 \text{ k}\Omega$				
	UNR421D		$V_{CC} = 5 \text{ V}, V_B = 10 \text{ V}, R_L = 1 \text{ k}\Omega$				
	UNR421E		$V_{CC} = 5 \text{ V}, V_B = 6 \text{ V}, R_L = 1 \text{ k}\Omega$				
Transition frequency		f_T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Input resistance	UNR4218	R_1		-30%	0.51	+30%	k Ω
	UNR4219				1.0		
	UNR4216/421F/421L				4.7		
	UNR4211/4214/4215/421K				10		
	UNR4212/4217				22		
	UNR4210/4213/421D/421E				47		
Resistance ratio	UNR4218/4219	R_1/R_2		0.08	0.10	0.12	—
	UNR4214			0.17	0.21	0.25	
	UNR421F			0.37	0.47	0.57	
	UNR4211/4212/4213/421L			0.8	1.0	1.2	
	UNR421K			1.70	2.13	2.60	
	UNR421E			1.70	2.14	2.60	
	UNR421D			3.7	4.7	5.7	

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

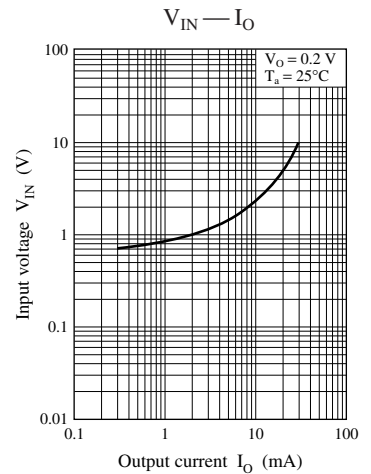
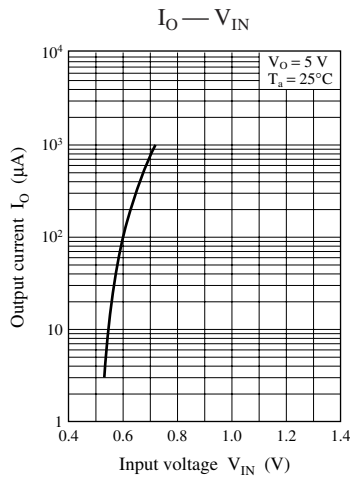
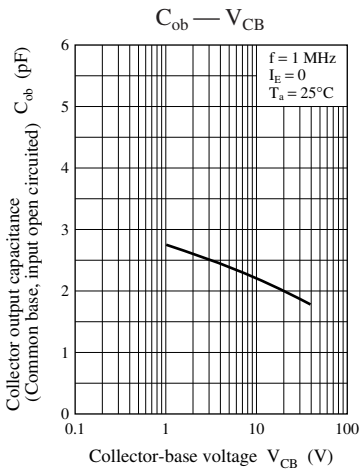
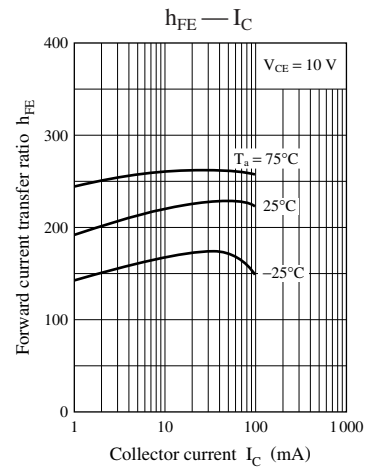
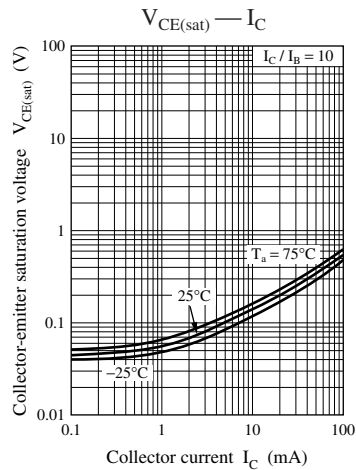
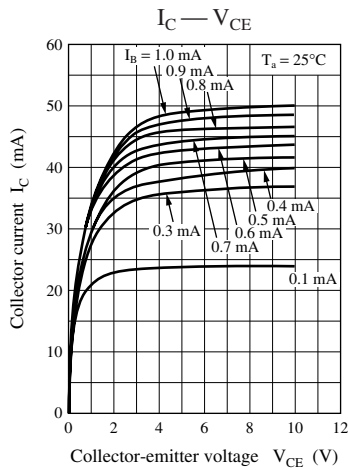
2. *: Rank classification

Rank	Q	R	S	No-rank
h_{FE}	160 to 260	210 to 340	290 to 460	160 to 460

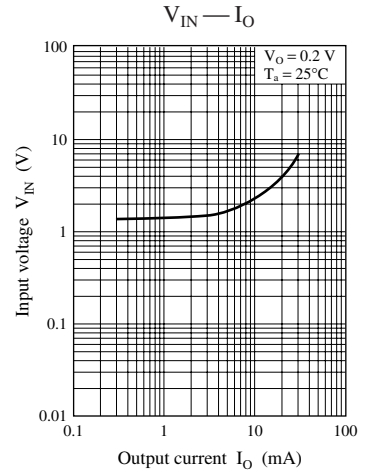
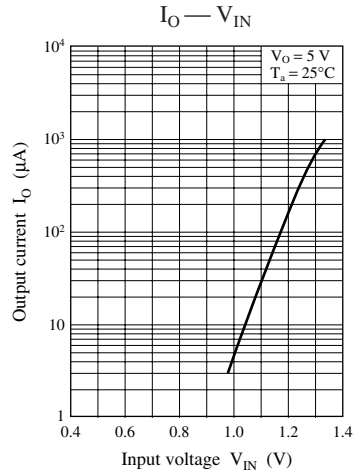
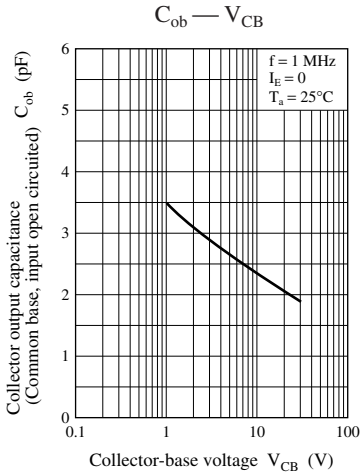
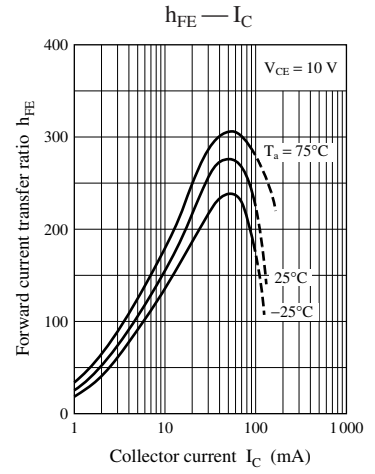
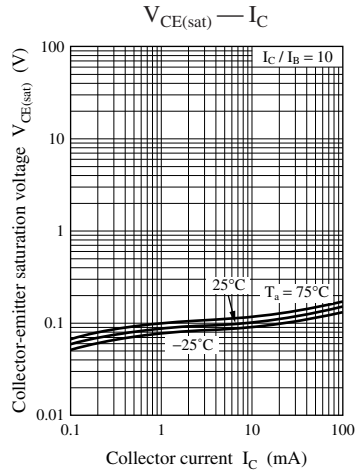
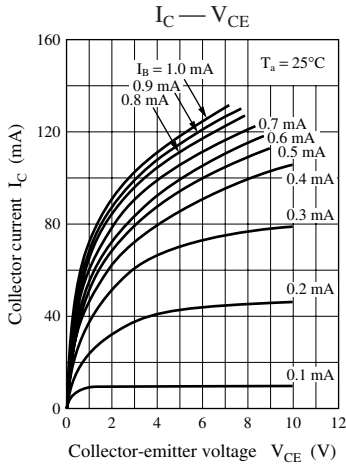
Common characteristics chart



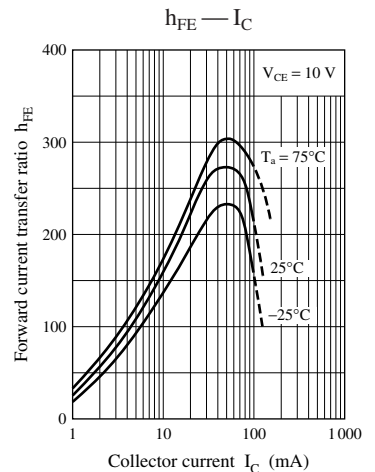
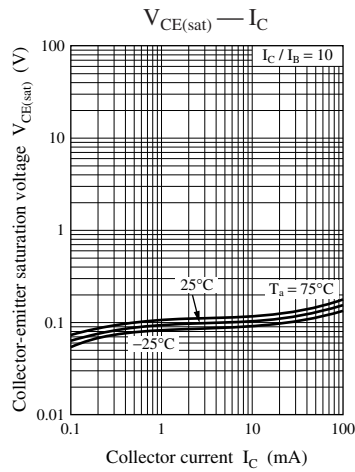
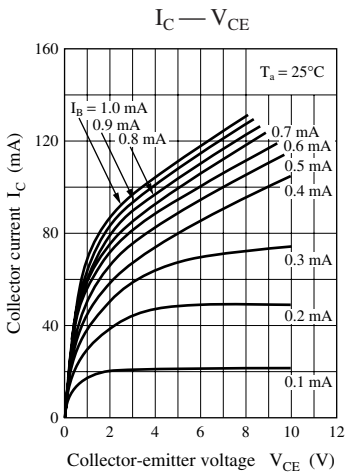
Characteristics charts of UNR4210

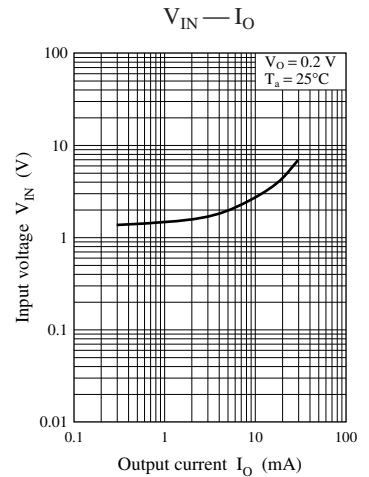
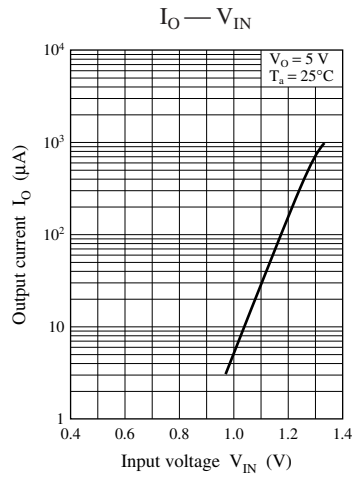
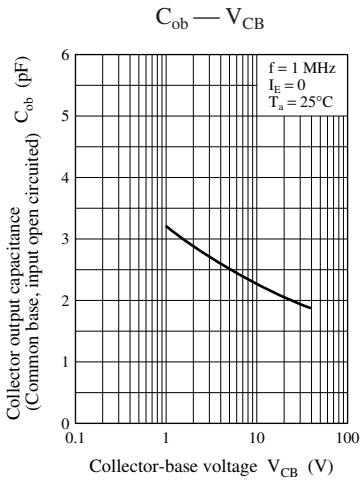


Characteristics charts of UNR4211

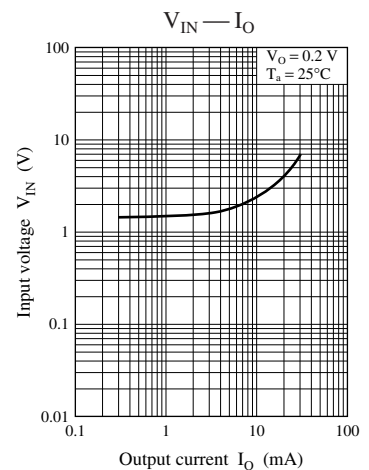
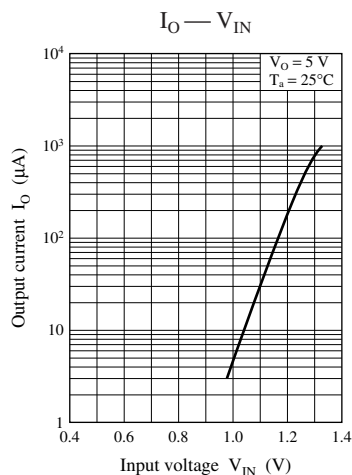
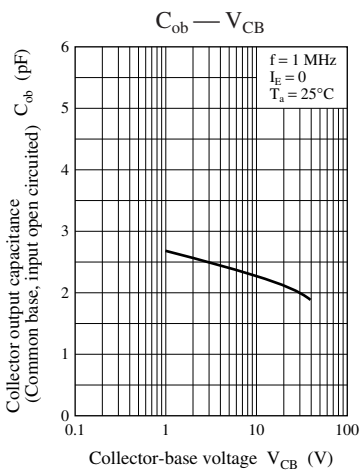
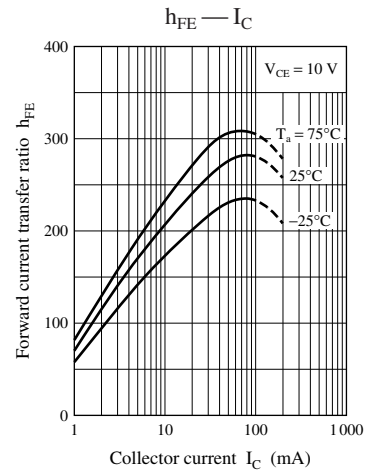
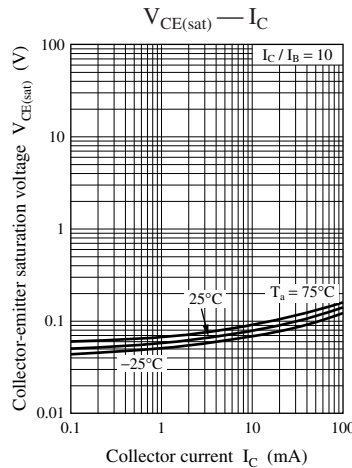
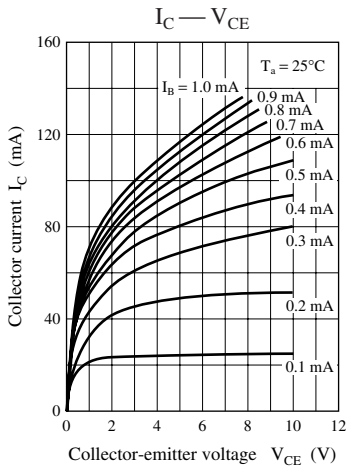


Characteristics charts of UNR4212

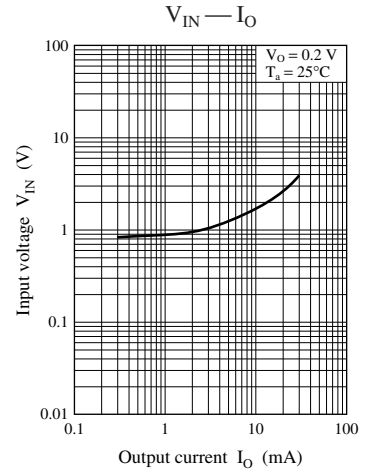
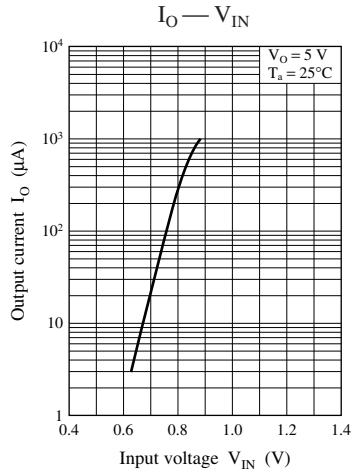
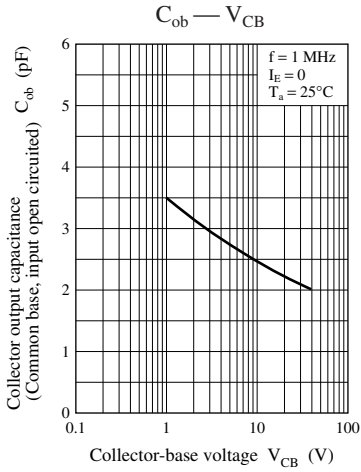
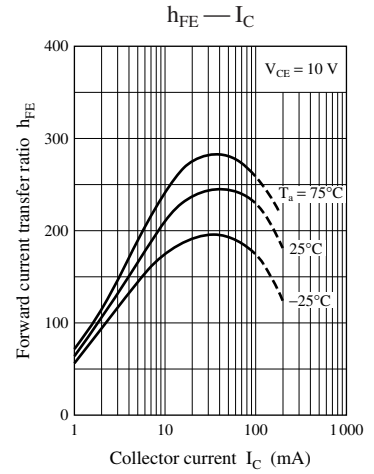
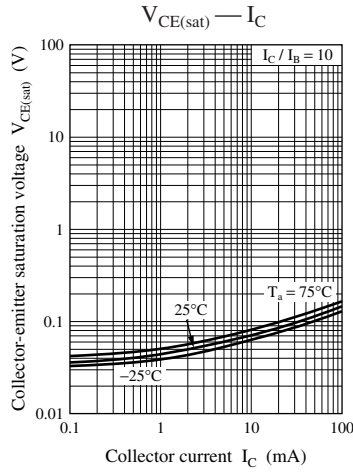
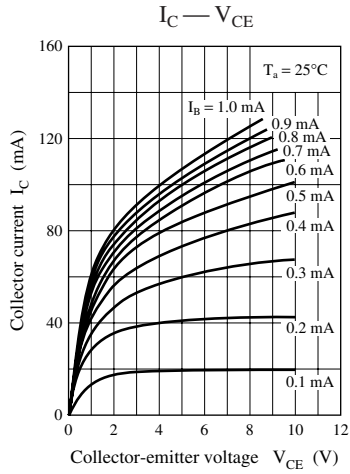




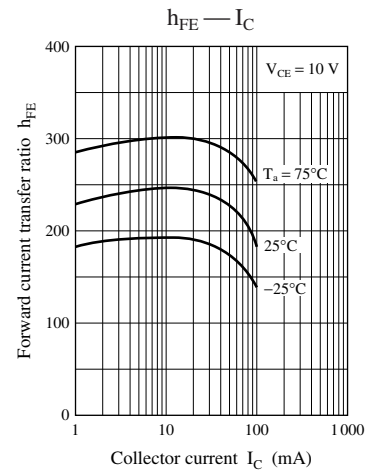
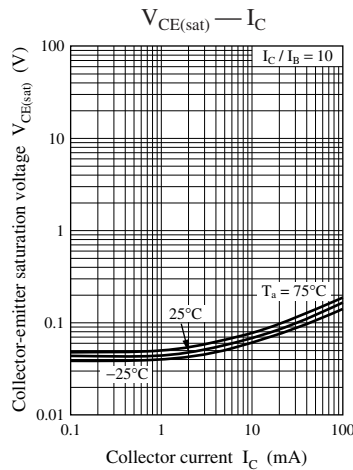
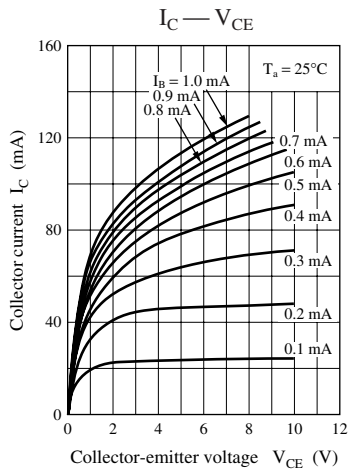
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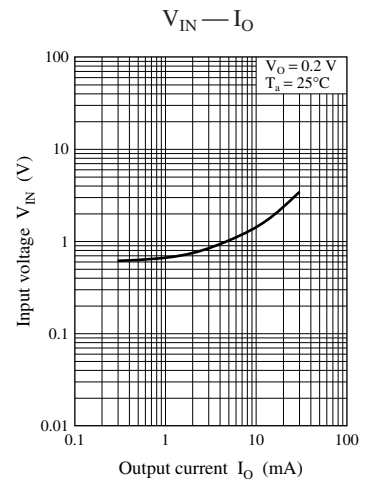
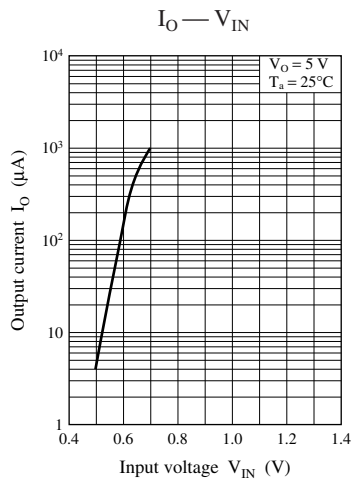
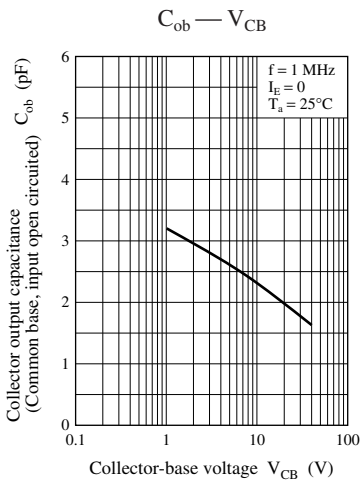


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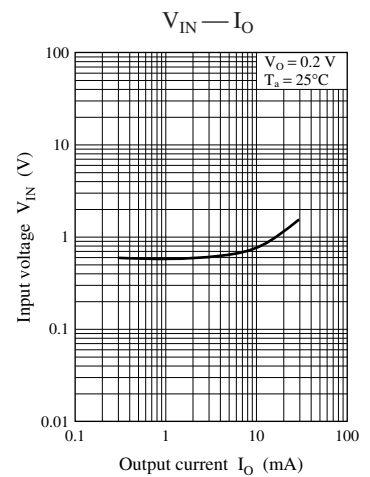
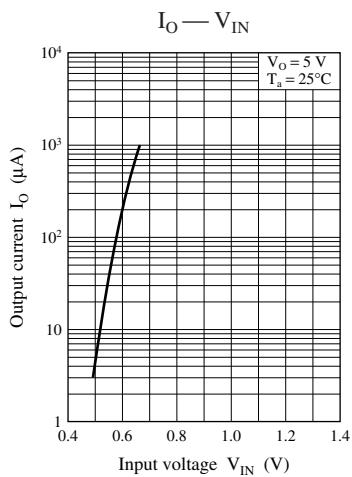
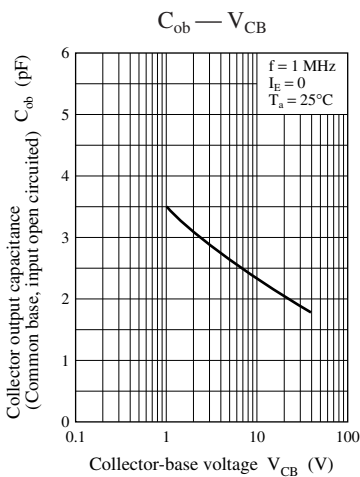
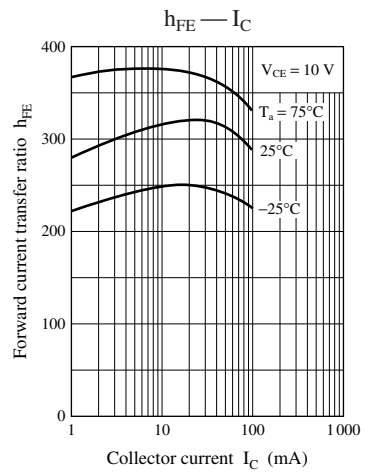
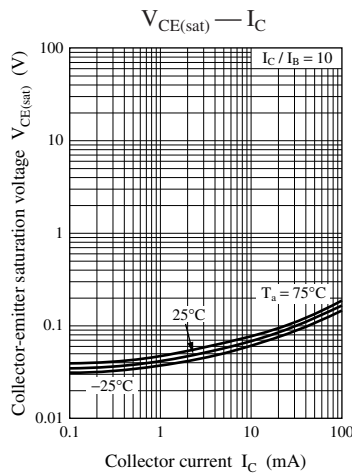
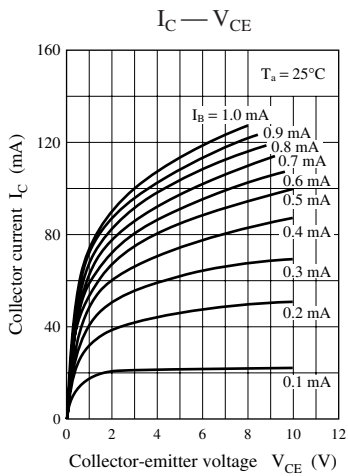


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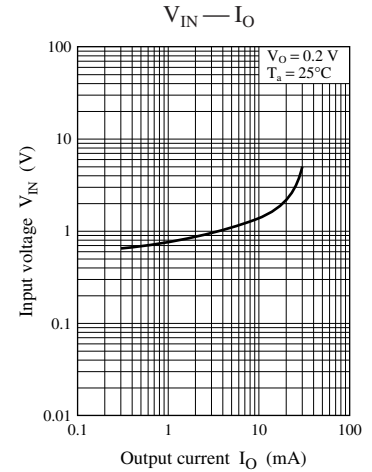
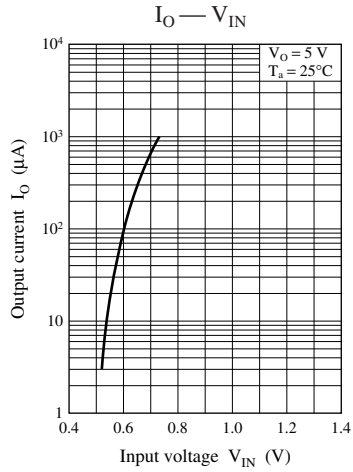
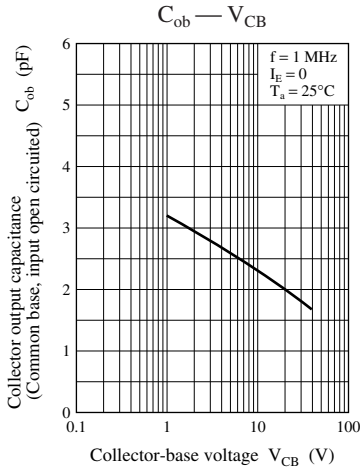
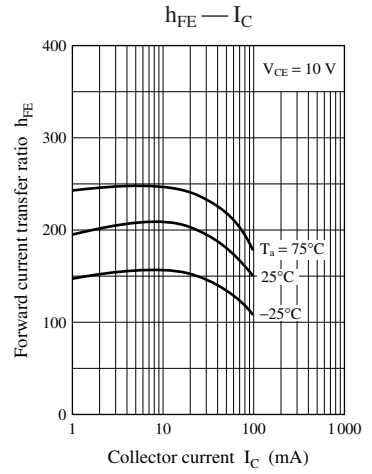
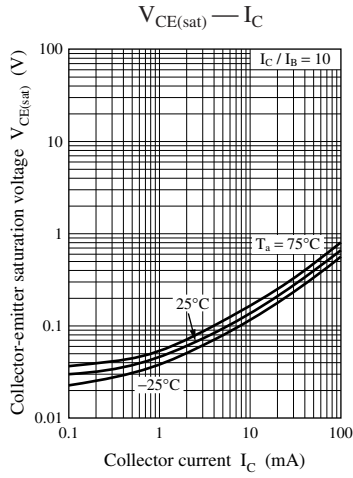
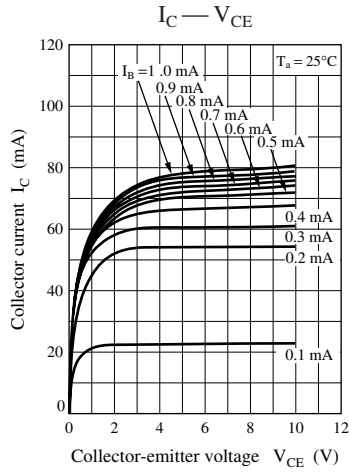




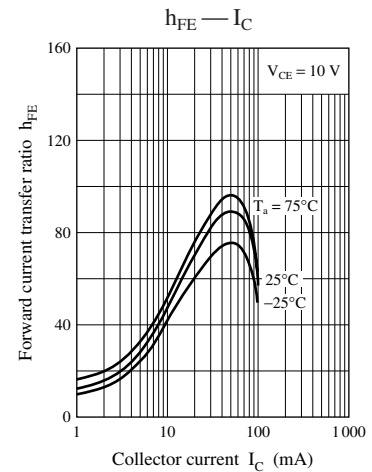
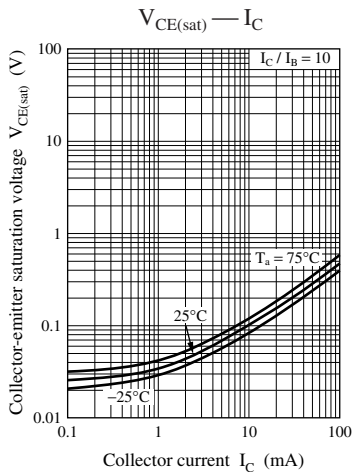
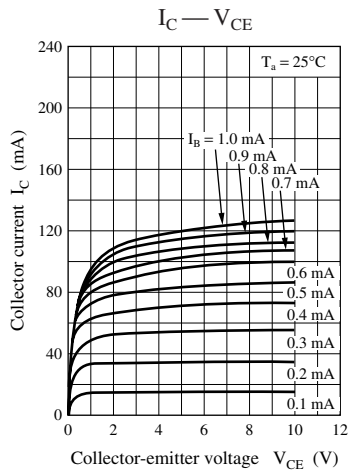
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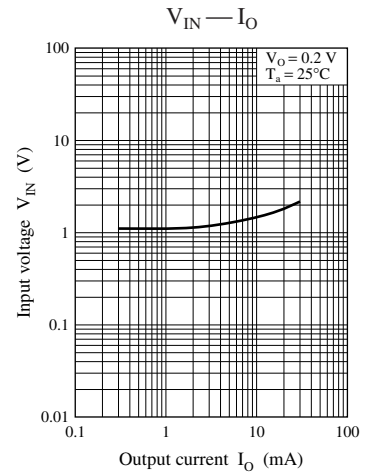
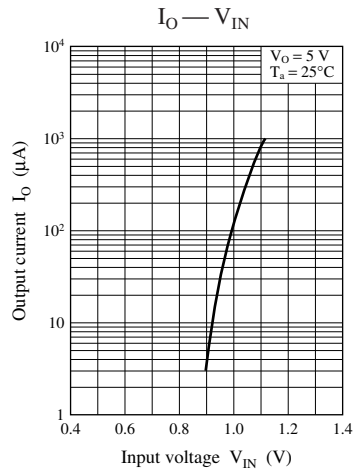
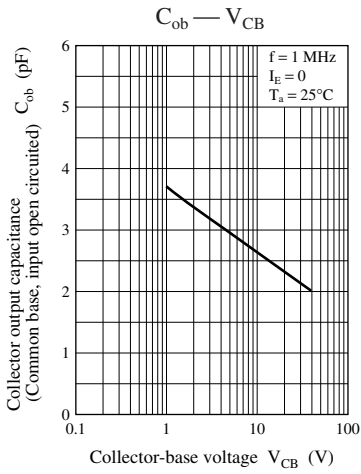


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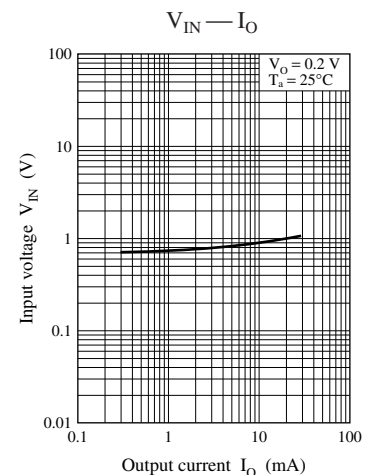
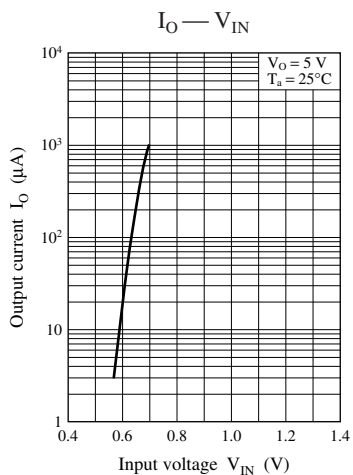
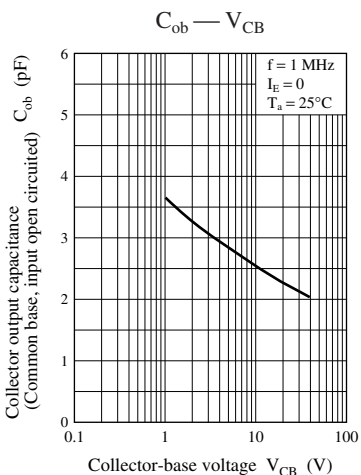
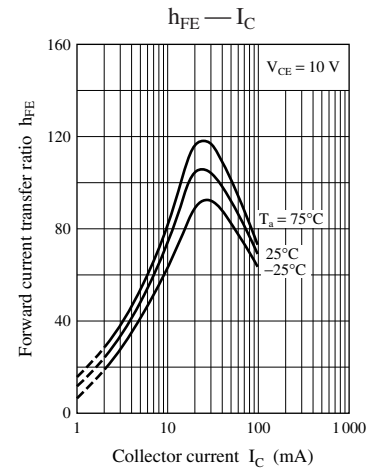
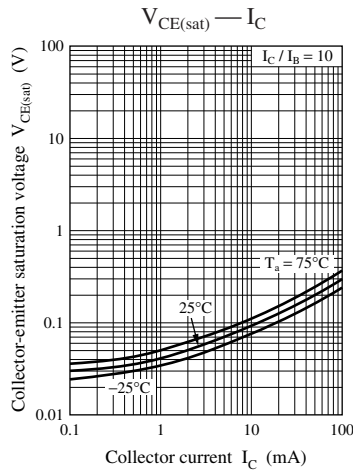
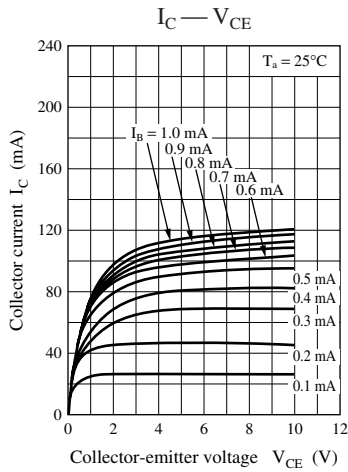


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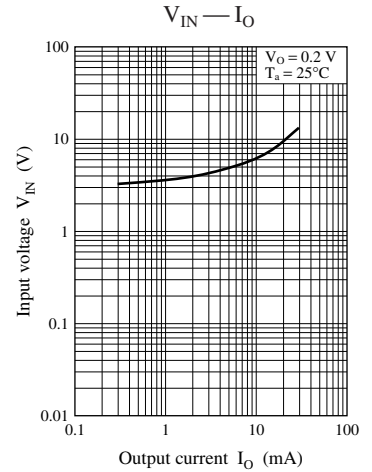
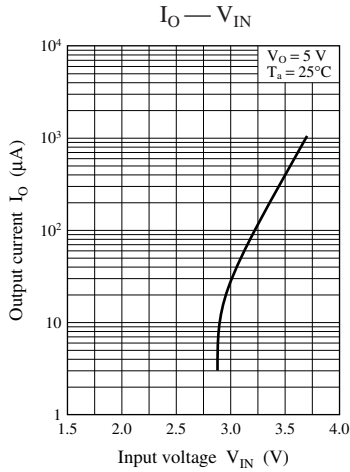
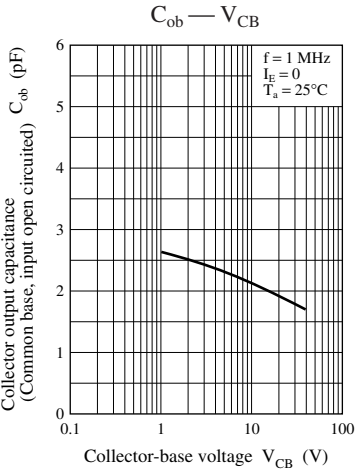
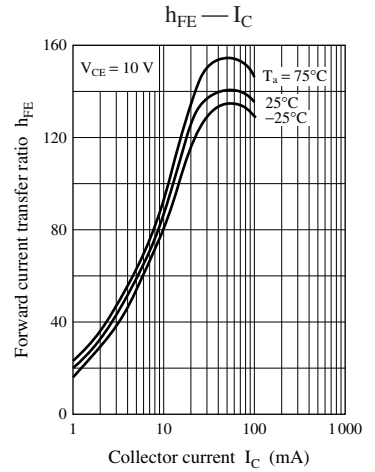
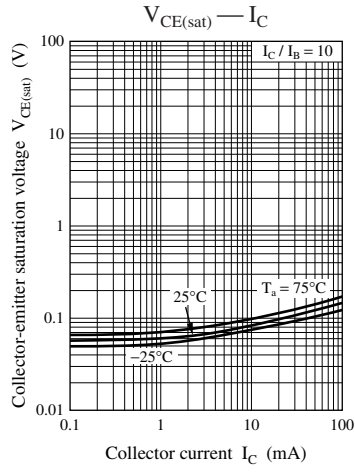
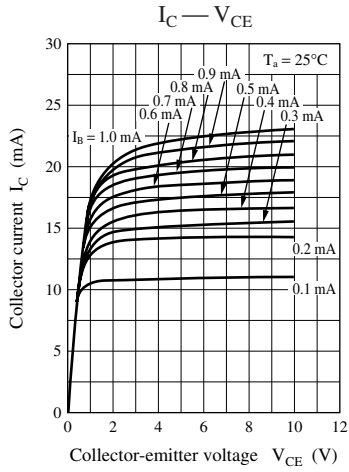




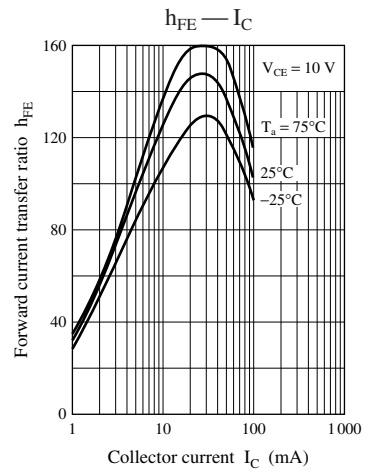
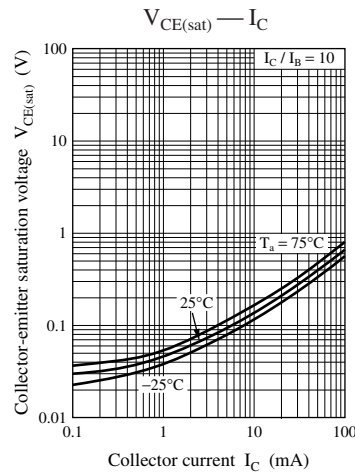
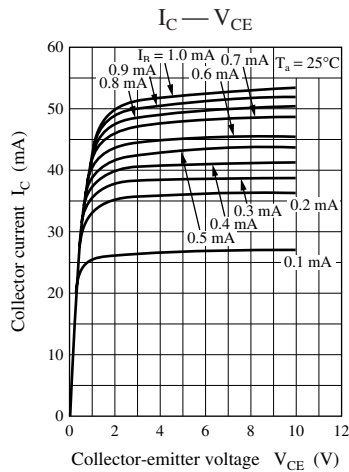
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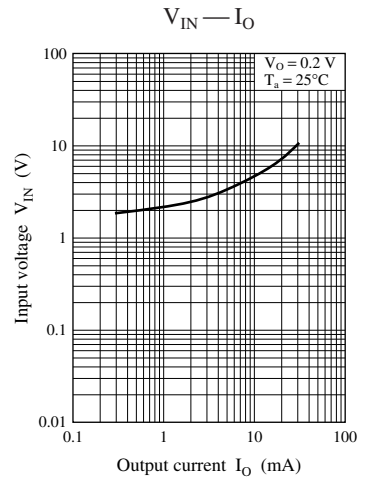
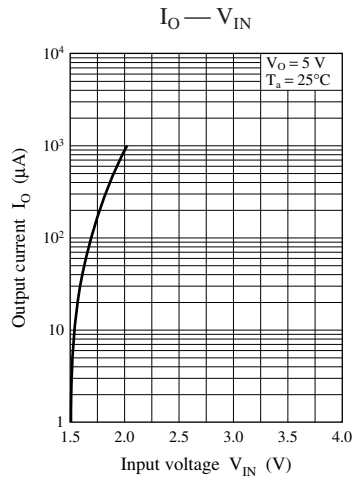
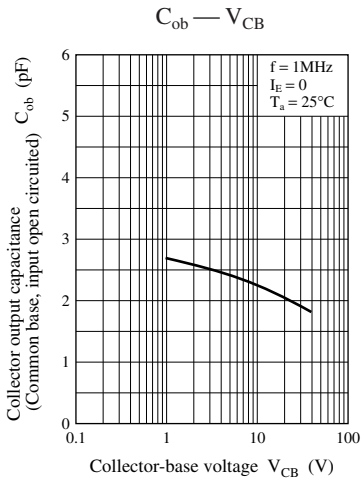


Characteristics charts of UNR421D

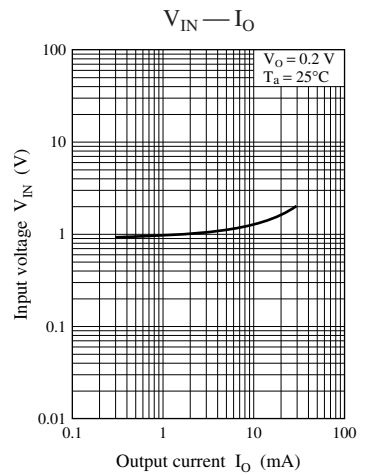
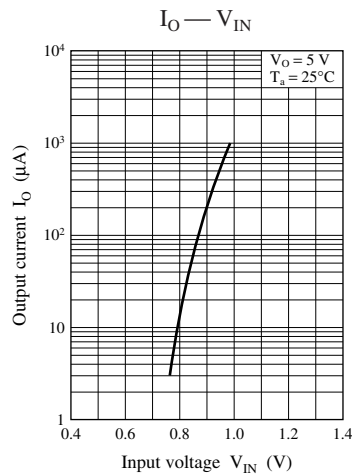
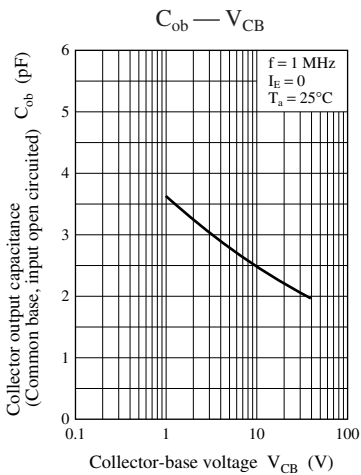
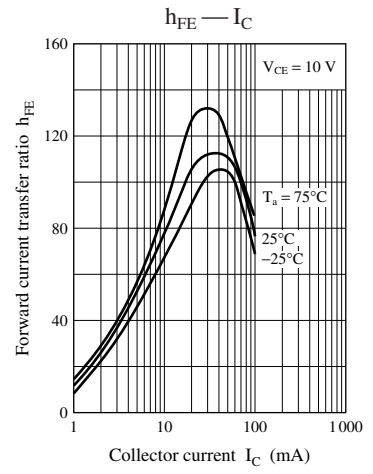
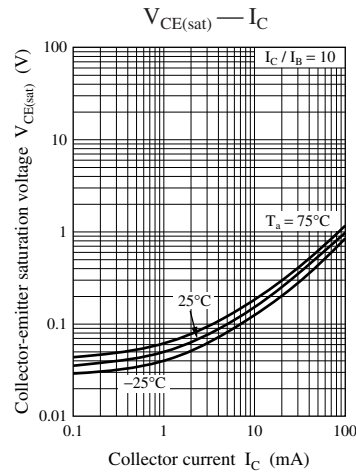
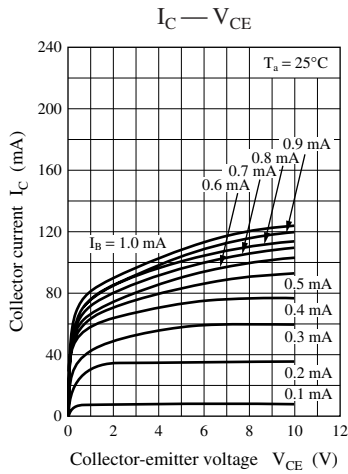


Characteristics charts of UNR421E

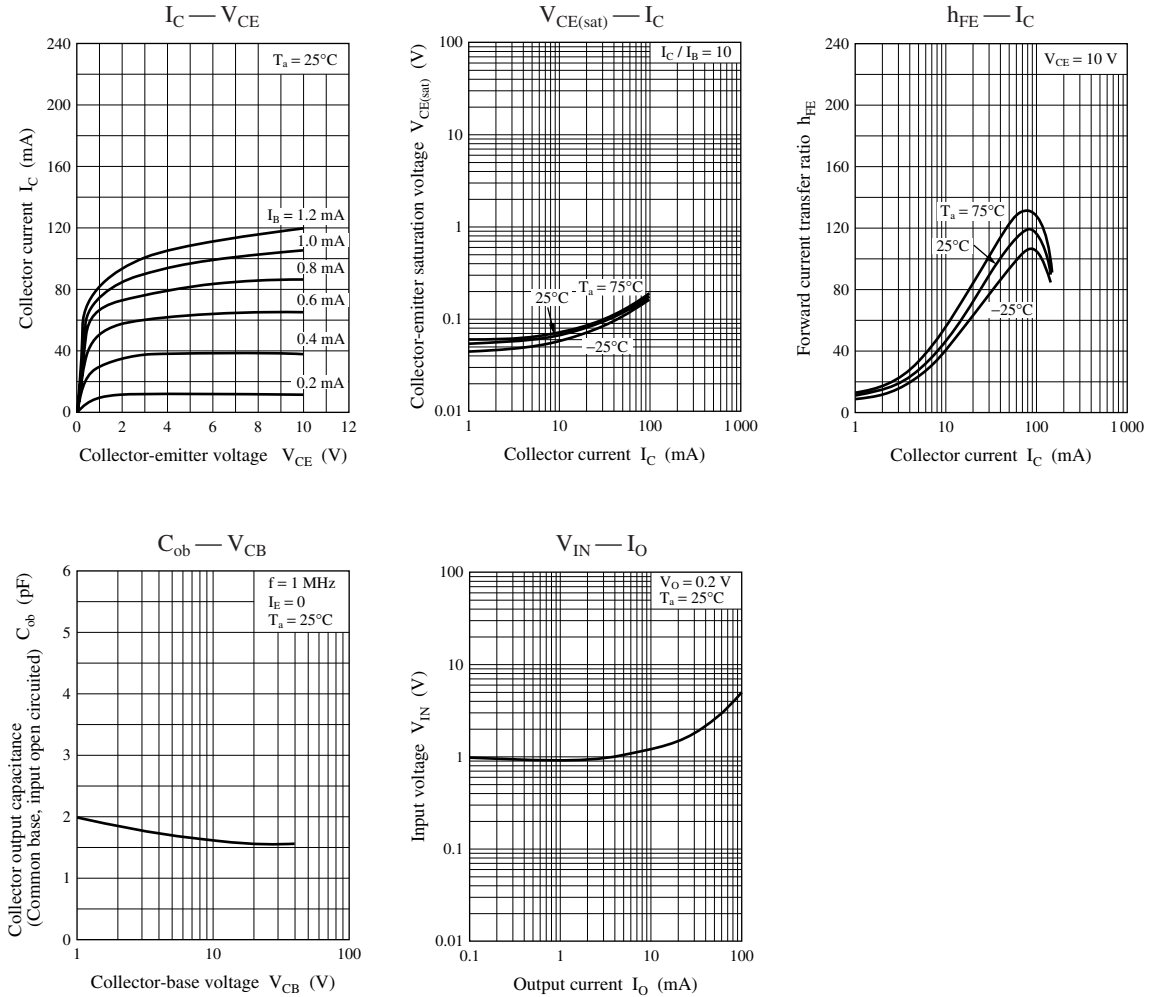




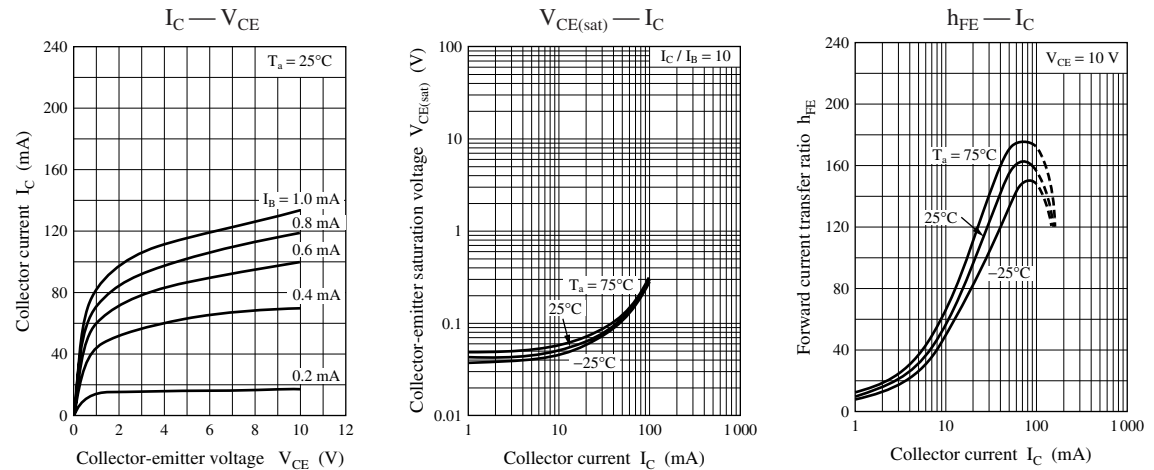
Characteristics charts of UNR421F

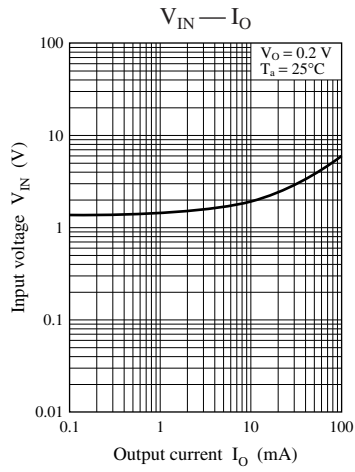
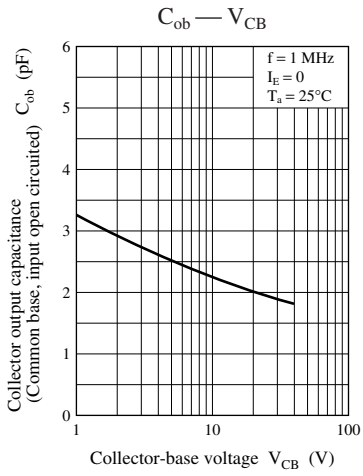


Characteristics charts of UNR421K



Characteristics charts of UNR421L





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